

12inch N-Type SiC Substrate



Parameter	Unit	Specification Value
Grade		Production Grade
Diameter	mm	300±0.5
Thickness	μm	600 ± 100
Doping		Nitrogen
Surface Orientation		4 °toward<11-20> ± 1°
Orientation flat		NA
Micropipe Density	cm ²	≤0.2
Resistivity (all)	Ω·cm	0.015~0.030
TTV	μm	≤ 10
Surface Roughness	nm	Si Face Ra≤0.5 nm, C Face Ra≤0.5 nm
Edge Chips		No edge chips with depth > 1mm
Laser marking		As per SEMI Standard
Polytype Area by polarized light		None permitted
Cracks by high-intensity light		None permitted
Packaging		Single Wafer Container; outer packing: no damage, no air leakage.